



A Product Line of
Diodes Incorporated



ZXTP03200BZ 200V PNP Low $V_{CE(sat)}$ transistor in SOT89

Summary

$BV_{CEO} > -200V$

$BV_{ECO} > -2V$

$I_{C(\text{cont})} = 2A$

$V_{CE(sat)} < -160mV @ -1A$

$R_{CE(sat)} = 130m\Omega$

$P_D = 2.4W$



Description

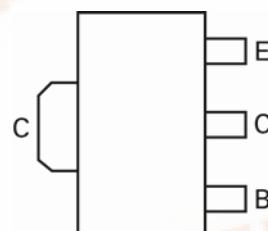
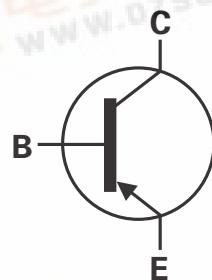
Packaged in the SOT89 outline this new 5th generation low saturation 200V PNP transistor offers extremely low on state losses making it ideal for use in DC-DC circuits and various driving and power management functions

Features

- 2 Amps continuous current
- Up to 5 Amps peak current
- Very low saturation voltage
- Enhanced switching performance

Applications

- DC-DC Convertors



Pinout - top view

Ordering Information

Device	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTP03200BZTA	7	12	1000

Device Marking

1N2

ZXTP03200BZ

Absolute Maximum Ratings

Parameter	Symbol	Limit	Unit
Collector-Base Voltage	V_{CBO}	-220	V
Collector-Emitter Voltage	V_{CEO}	-200	V
Emitter-Base Voltage	V_{EBO}	-7	V
Continuous Collector Current ^(a)	I_C	-2	A
Base Current	I_B	-1	A
Peak Pulse Current	I_{CM}	-5	A
Power Dissipation at $T_A=25^\circ\text{C}$ ^(a) Linear Derating Factor	P_D	1.1 8.8	W mW/ $^\circ\text{C}$
Power Dissipation at $T_A=25^\circ\text{C}$ ^(b) Linear Derating Factor	P_D	1.8 14.4	W mW/ $^\circ\text{C}$
Power Dissipation at $T_A=25^\circ\text{C}$ ^(c) Linear Derating Factor	P_D	2.4 19.2	W mW/ $^\circ\text{C}$
Power Dissipation at $T_A=25^\circ\text{C}$ ^(d) Linear Derating Factor	P_D	4.46 35.7	W mW/ $^\circ\text{C}$
Power Dissipation at $T_C=25^\circ\text{C}$ ^(e) Linear Derating Factor	P_D	38.7 309.6	W mW/ $^\circ\text{C}$
Operating and Storage Temperature Range	T_j, T_{stg}	-55 to 150	$^\circ\text{C}$

Thermal Resistance

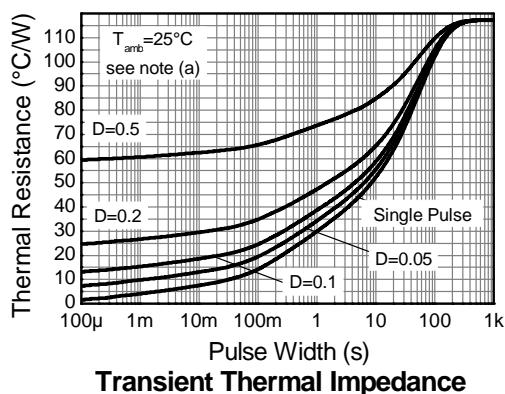
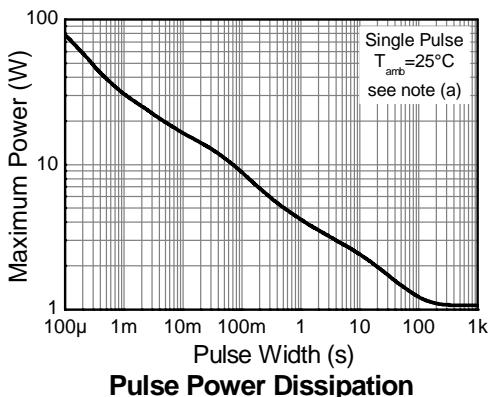
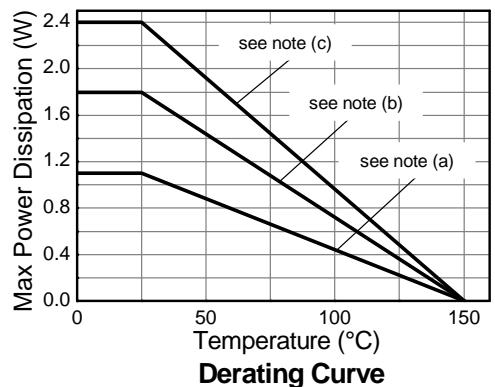
Parameter	Symbol	Value	Unit
Junction to Ambient ^(a)	$R_{\theta JA}$	117	$^\circ\text{C/W}$
Junction to Ambient ^(b)	$R_{\theta JA}$	68	$^\circ\text{C/W}$
Junction to Ambient ^(c)	$R_{\theta JA}$	51	$^\circ\text{C/W}$
Junction to Ambient ^(d)	$R_{\theta JA}$	28	$^\circ\text{C/W}$
Junction to Lead ^(e)	$R_{\theta JL}$	3.23	$^\circ\text{C/W}$

NOTES:

- (a) For a device surface mounted on 15mm x 15mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.
- (b) Mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.
- (c) Mounted on 50mm x 50mm x 1.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions.
- (d) As (c) above measured at $t < 5$ seconds.
- (e) Junction to Lead from Collector Tab. Typical

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Thermal Characteristics



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Electrical Characteristics (at $T_{amb} = 25^\circ C$ unless otherwise stated)

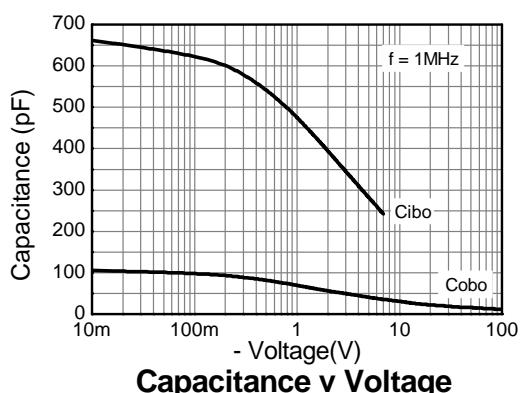
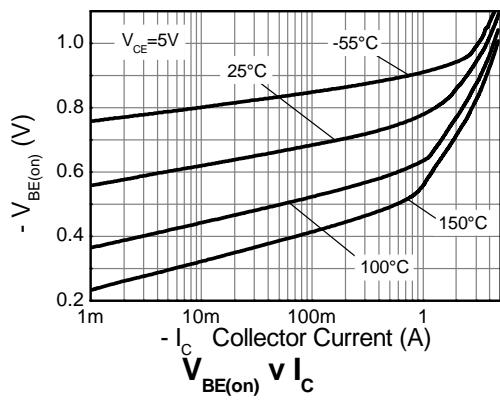
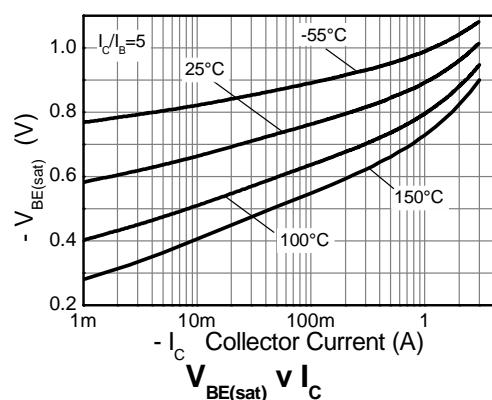
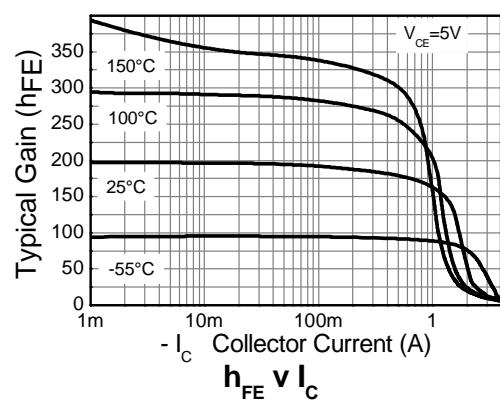
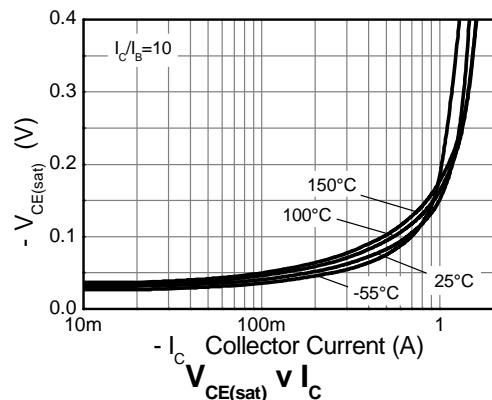
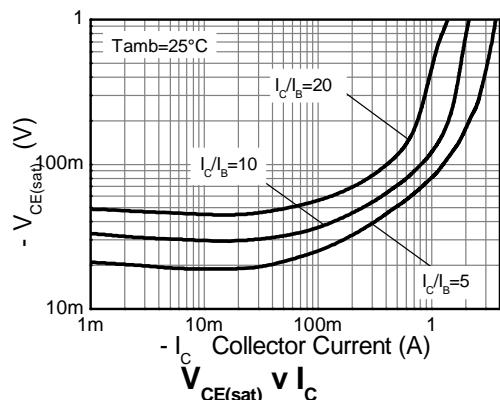
Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-Base Breakdown Voltage	BV_{CBO}	-220	-245		V	$I_C = -100\mu A$
Collector-Emitter Breakdown voltage	BV_{CER}	-220	-245		V	$I_C = -1\mu A, R_{BE} \leq 1k\Omega$
Collector-Emitter Breakdown Voltage	BV_{CEO}	-200	-225		V	$I_C = -10mA$ (*)
Emitter-Base Breakdown Voltage	BV_{EBO}	-7	-8.4		V	$I_E = -100\mu A$
Collector-Base Cut-off Current	I_{CBO}		<1	-50 -0.5	nA μA	$V_{CB} = -200V$ $V_{CB} = -200V, T_{amb} = 100^\circ C$
Emitter Cut-off Current	I_{EBO}		<1	-10	nA	$V_{EB} = -6V$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		-37 -120 -130 -160	-50 -155 -160 -260	mV mV mV mV	$I_C = -0.1A, I_B = -10mA$ (*) $I_C = -0.5A, I_B = -25mA$ (*) $I_C = -1A, I_B = -100mA$ (*) $I_C = -2A, I_B = -400mA$ (*)
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		-940	-1100	mV	$I_C = -2A, I_B = -400mA$ (*)
Base-Emitter Turn-on Voltage	$V_{BE(on)}$		-840	-1000	mV	$I_C = -2A, V_{CE} = -5V$ (*)
Static Forward Current Transfer Ratio	h_{FE}	100 100 20	195 170 50 5	300		$I_C = -10mA, V_{CE} = -5V$ (*) $I_C = -1A, V_{CE} = -5V$ (*) $I_C = -2A, V_{CE} = -5V$ (*) $I_C = -5A, V_{CE} = -5V$ (*)
Transition Frequency	f_T		105		MHz	$I_C = -100mA, V_{CE} = -10V$ $f = 50MHz$
Output Capacitance	C_{obo}		31		pF	$V_{CB} = -10V, f = 1MHz$ (*)
Delay Time	t_d		21		ns	$I_C = -1A, V_{CC} = -50V$, $I_{B1} = -I_{B2} = -100mA$
Rise Time	t_r		18		ns	
Storage Time	t_s		680		ns	
Fall Time	t_f		75		ns	

NOTES:

(*) Measured under pulsed conditions. Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$.

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Typical Characteristics

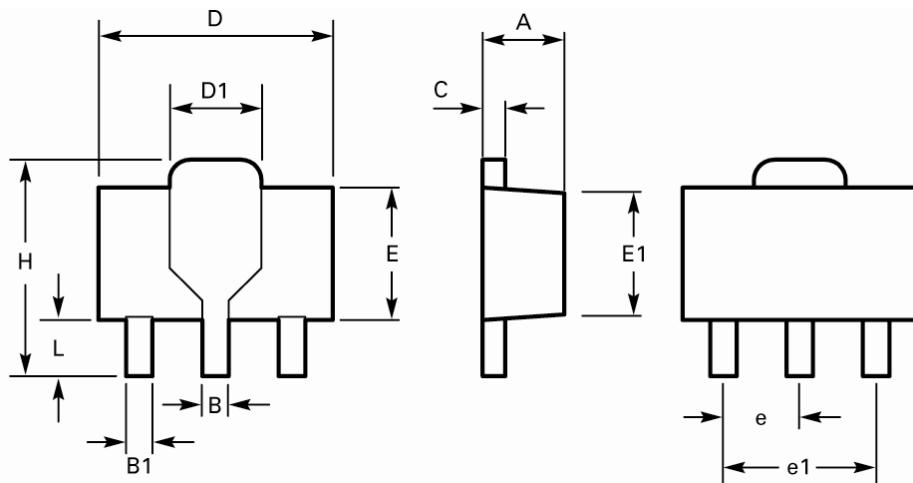


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Package Information –SOT89



DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min	Max	Min	Max		Min	Max	Min	Max
A	1.40	1.60	0.550	0.630	e	1.40	1.50	0.055	0.059
b	0.38	0.48	0.015	0.019	E	3.75	4.25	0.150	0.167
b1	-	0.53	-	0.021	E1	-	2.60	-	0.102
b2	1.50	1.80	0.060	0.071	G	2.90	3.00	0.114	0.118
c	0.28	0.44	0.011	0.017	H	2.60	2.85	0.102	0.112
D	4.40	4.60	0.173	0.181	-	-	-	-	-

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- or
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"Active"	Product status recommended for new designs
"Last time buy (LTB)"	Device will be discontinued and last time buy period and delivery is in effect
"Not recommended for new designs"	Device is still in production to support existing designs and production
"Obsolete"	Production has been discontinued

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